FAIRCHILD

SEMICONDUCTOR TM

### January 1993 Revised August 2000

# SCAN182373A Transparent Latch with 25Ω Series Resistor Outputs

#### **General Description**

The SCAN182373A is a high performance BiCMOS transparent latch featuring separate data inputs organized into dual 9-bit bytes with byte-oriented latch enable and output enable control signals. This device is compliant with IEEE 1149.1 Standard Test Access Port and Boundary-Scan Architecture with the incorporation of the defined boundaryscan test logic and test access port consisting of Test Data Input (TDI), Test Data Out (TDO), Test Mode Select (TMS), and Test Clock (TCK).

#### Features

- IEEE 1149.1 (JTAG) Compliant
- High performance BiCMOS technology
- 25Ω series resistor outputs eliminate need for external terminating resistors
- Buffered active-low latch enable
- 3-STATE outputs for bus-oriented applications
- 25 mil pitch SSOP (Shrink Small Outline Package)
- Includes CLAMP, IDCODE and HIGHZ instructions
- Additional instructions SAMPLE-IN, SAMPLE-OUT and EXTEST-OUT
- Power up 3-STATE for hot insert
- Member of Fairchild's SCAN Products

#### **Ordering Code:**

Order Number	Package Number	Package Description
SCAN182373ASSC	MS56A	56-Lead Shrink Small Outline Package (SSOP), JEDEC MO-118, 0.300 Wide

Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.

#### Connection Diagram

$AO_0 = 2$ $AO_1 = 2$ $AO_1 = 2$ $AO_2 = 2$ $GND = 4$ $AO_3 = 2$ $AO_4 = 2$ $AO_5 = 2$ $AO_6 = 2$	1 2 3 4 4 5 5 5 7 8 9 9 10 0 11	56 55 54 53 51 50 49 48 47 46	TDI Alo ALE Al <sub>1</sub> Al <sub>2</sub> GND Al <sub>3</sub> Al <sub>4</sub> V <sub>CC</sub> Al <sub>5</sub>
$\begin{array}{c} \overline{AOE_1} \\ \overline{AO_2} \\ \overline{CND} \\ \overline{CND} \\ \overline{AO_3} \\ \overline{COC} \\ \overline{COC} \\ \overline{AO_5} \\ \overline{AO_6} \end{array}$	3 4 5 5 7 8 9 10	54 52 51 50 49 48 47	ALE AI <sub>1</sub> GND AI <sub>3</sub> AI <sub>4</sub> V <sub>CC</sub>
$\begin{array}{c} \overline{AOE_1} \\ \overline{AO_2} \\ \overline{CND} \\ \overline{CND} \\ \overline{AO_3} \\ \overline{COC} \\ \overline{COC} \\ \overline{AO_5} \\ \overline{AO_6} \end{array}$	4 5 5 7 8 9 10	54 52 51 50 49 48 47	ALE AI <sub>1</sub> GND AI <sub>3</sub> AI <sub>4</sub> V <sub>CC</sub>
A01 A02 GND A03 A04 V <sub>CC</sub> A05 A06	5 5 7 8 9 10	52 51 50 49 48 47	Al <sub>1</sub> Al <sub>2</sub> GND Al <sub>3</sub> Al <sub>4</sub> V <sub>CC</sub>
$\begin{array}{c} AO_2 \\ GND \\ AO_3 \\ AO_4 \\ V_{CC} \\ AO_5 \\ AO_6 \end{array}$	5 7 8 9 10	51 50 49 48 47	Al2 GND Al3 Al4 VCC
GND = 0 $AO_3 = 1$ $AO_4 = 0$ $V_{CC} = 0$ $AO_5 = 1$	7 8 9 10	50 49 48 47	GND Al <sub>3</sub> Al <sub>4</sub> V <sub>CC</sub>
A03 - 1 A04 - 1 V <sub>CC</sub> - 9 A05 - 1	8 9 10	49 48 47	- AI3 - AI4 - V <sub>CC</sub>
A04 - 1 V <sub>CC</sub> - 1 A05 - 1 A06 - 1	9	<b>4</b> 8 47	– AI <sub>4</sub> – V <sub>CC</sub>
V <sub>CC</sub> - 1 AO <sub>5</sub> - 1 AO <sub>6</sub> - 1	10	47	-v <sub>cc</sub>
ао <sub>5</sub> — 1 ао <sub>6</sub> — 1			- AI5
ао <sub>6</sub> — 1	11	46	
			- Al <sub>6</sub>
GND - 1	12	45	— GND
A07 -	13	44	- Al7
	14	43	- AI8
	15	42	— ВІ <sub>О</sub>
	16	41	— ві,
GND -	17	40	— GND
во <sub>2</sub> — 1	18	39	— ві <sub>2</sub>
	19	38	— BI3
	20	37	-v <sub>cc</sub>
	2 1	36	— BI4
	22	35	-BI5
	23	34	— GND
во <sub>6</sub> — :	24	33	— ві <sub>6</sub>
BO <sub>7</sub> — 3	25	32	— ві <sub>7</sub>
BOE1-	26	31	BLE
во <sub>8</sub> — :	27	30	— ві <sub>8</sub>
TDO —	28	29	— тск

#### **Pin Descriptions**

Pin Names	Description	ĺ
AI <sub>(0-8)</sub> , BI <sub>(0-8)</sub> ALE, BLE	Data Inputs	
ALE, BLE	Latch Enable Inputs	
$\overline{AOE}_1, \overline{BOE}_1$	3-STATE Output Enable Inputs	
AO <sub>(0-8)</sub> , BO <sub>(0-8)</sub>	3-STATE Latch Outputs	

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#### **Truth Tables**

L = LOW Voltage Level

Z = High Impedance

X = Immaterial

	Inputs		
ALE	†AOE <sub>1</sub>	AI (0–8)	AO (0–8)
Х	Н	Х	Z
н	L	L	L
н	L	н	н
L	L	Х	AO <sub>0</sub>
H = HIGH Voltage I	_evel	·	

	Inputs					
BLE	†BOE <sub>1</sub>	BI (0–8)	BO (0–8)			
Х	Н	Х	Z			
н	L	L	L			
н	L	н	н			
L	L	Х	BO <sub>0</sub>			

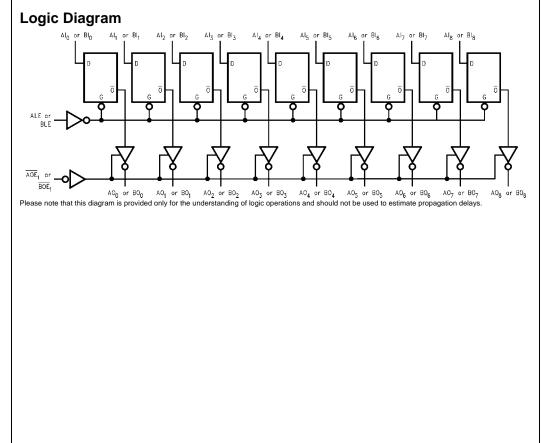
 $BO_0 = Previous BO before H-to-L transition of BLE$ 

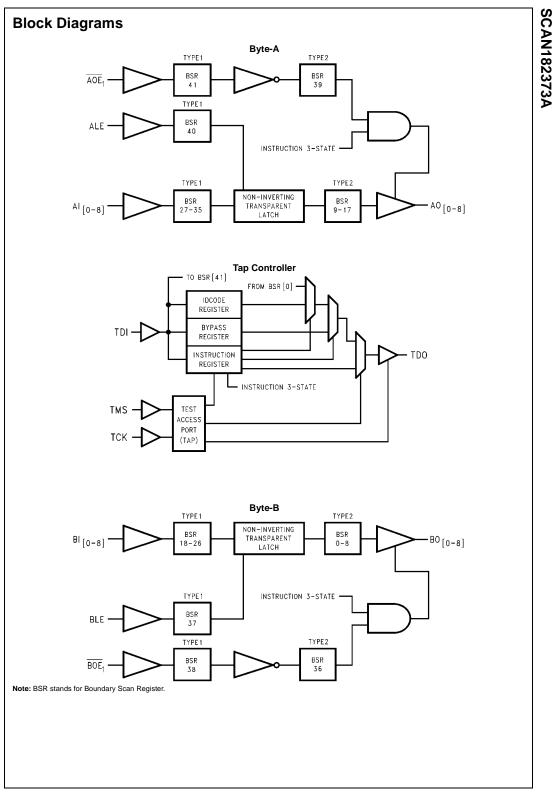
t = Inactive-to-active transition must occur to enable outputs upon power-up.

#### **Functional Description**

The SCAN182373A consists of two sets of nine D-type latches with 3-STATE standard outputs. When the Latch Enable (ALE or BLE) input is HIGH, data on the inputs (Al<sub>(0-8)</sub> or Bl<sub>(0-8)</sub>) enters the latches. In this condition the latches are transparent, i.e., a latch output will change state each time its input changes. When Latch Enable is LOW, the latches store the information that was present on

the inputs a set-up time preceding the HIGH-to-LOW transition of the Latch Enable. The 3-STATE standard outputs are controlled by the Output Enable ( $\overline{AOE}_1$  or  $\overline{BOE}_1$ ) input. When Output Enable is LOW, the standard outputs are in the 2-state mode. When Output Enable is HIGH, the standard outputs are in the high impedance mode, but this does not interfere with entering new data into the latches.



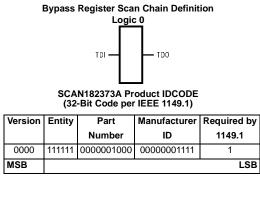


## **Description of BOUNDARY-SCAN Circuitry**

The scan cells used in the BOUNDARY-SCAN register are one of the following two types depending upon their location. Scan cell TYPE1 is intended to solely observe system data, while TYPE2 has the additional ability to control system data.

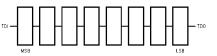
Scan cell TYPE 1 is located on each system input pin while scan cell TYPE2 is located at each system output pin as well as at each of the two internal active-high output enable signals. AOE controls the activity of the A-outputs while BOE controls the activity of the B-outputs. Each will activate their respective outputs by loading a logic high.

The BYPASS register is a single bit shift register stage identical to scan cell TYPE1. It captures a fixed logic low.



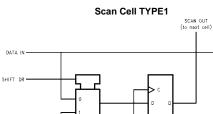
The INSTRUCTION register is an 8-bit register which captures the default value of 10000001 (SAMPLE/PRELOAD) during the CAPTURE-IR instruction command. The benefit of capturing SAMPLE/PRELOAD as the default instruction during CAPTURE-IR is that the user is no longer required to shift in the 8-bit instruction for SAMPLE/PRELOAD. The sequence of: CAPTURE-IR  $\rightarrow$  EXIT1-IR  $\rightarrow$  UPDATE-IR will update the SAMPLE/PRELOAD instruction. For more information refer to the section on instruction definitions.

Instruction Register Scan Chain Definition



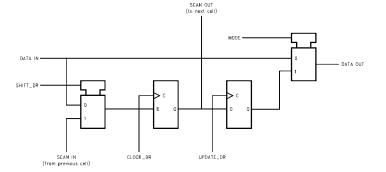
MSB $\rightarrow$ LSB	
Instruction Code	Instruction
0000000	EXTEST
1000001	SAMPLE/PRELOAD
10000010	CLAMP
00000011	HIGH-Z
01000001	SAMPLE-IN
01000010	SAMPLE-OUT
00100010	EXTEST-OUT
10101010	IDCODE
1111111	BYPASS
All Others	BYPASS

DATA OUT



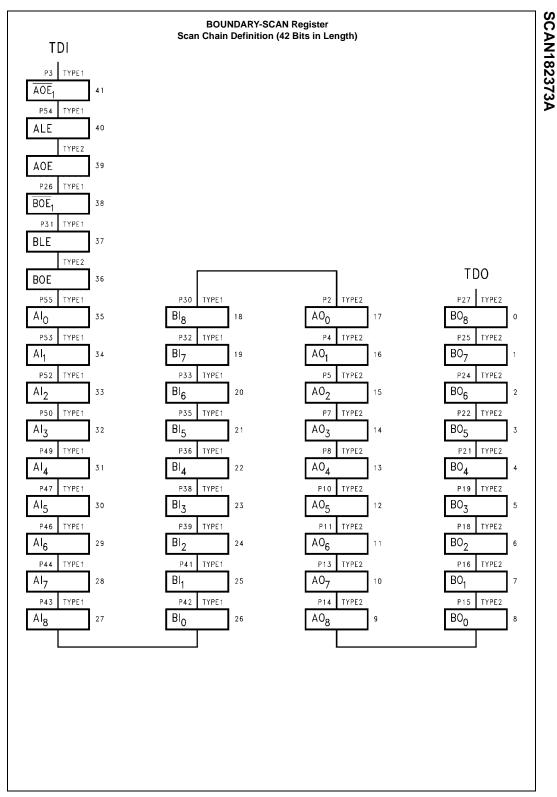
SCAN IN (from previous cell) MOD

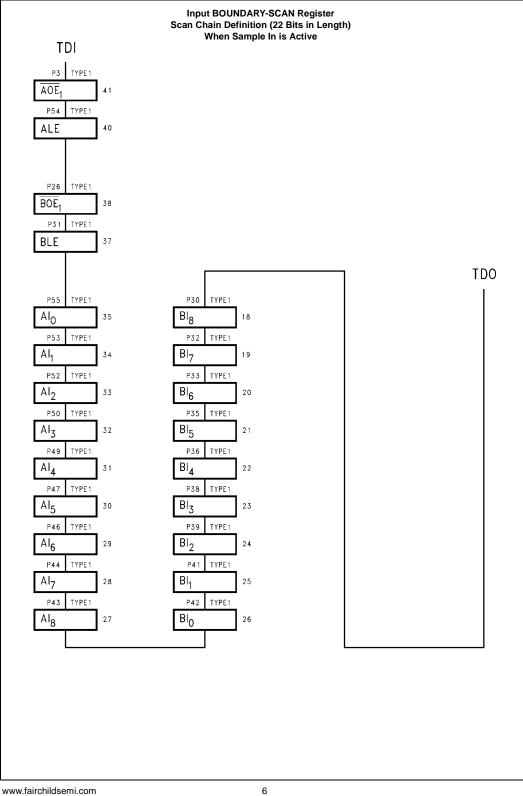




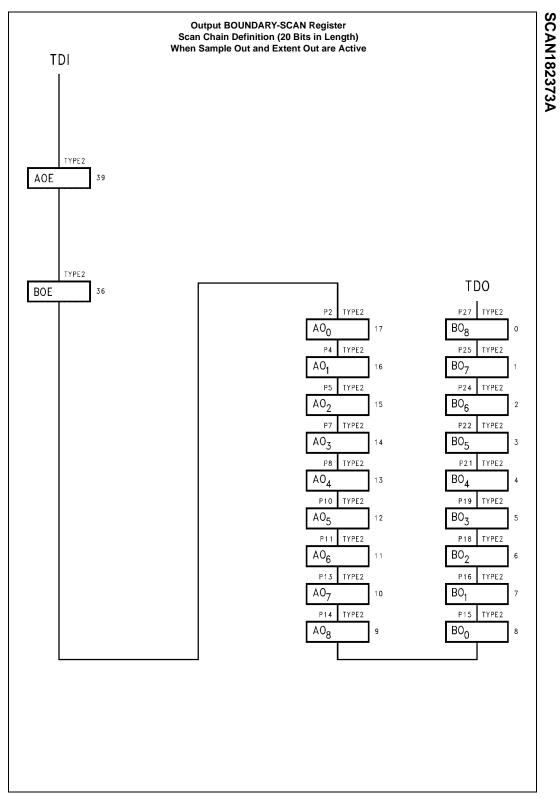
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Bit No.	Pin Name	Pin No.	Pin Type	Scan C	ell Type
41	AOE <sub>1</sub>	3	Input	TYPE1	
40	ALE	54	Input	TYPE1	
39	AOE		Internal	TYPE2	Control
38	BOE <sub>1</sub>	26	Input	TYPE1	Signals
37	BLE	31	Input	TYPE1	
36	BOE		Internal	TYPE2	
35	AI <sub>0</sub>	55	Input	TYPE1	
34	AI <sub>1</sub>	53	Input	TYPE1	
33	Al <sub>2</sub>	52	Input	TYPE1	
32	AI <sub>3</sub>	50	Input	TYPE1	
31	Al <sub>4</sub>	49	Input	TYPE1	A-in
30	AI <sub>5</sub>	47	Input	TYPE1	
29	AI <sub>6</sub>	46	Input	TYPE1	
28	AI <sub>7</sub>	44	Input	TYPE1	
27	AI <sub>8</sub>	43	Input	TYPE1	
26	BI <sub>0</sub>	42	Input	TYPE1	
25	BI <sub>1</sub>	41	Input	TYPE1	
24	BI <sub>2</sub>	39	Input	TYPE1	
23	BI <sub>3</sub>	38	Input	TYPE1	
22	BI <sub>4</sub>	36	Input	TYPE1	B-in
21	BI <sub>5</sub>	35	Input	TYPE1	
20	BI <sub>6</sub>	33	Input	TYPE1	
19	BI <sub>7</sub>	32	Input	TYPE1	
18	BI <sub>8</sub>	30	Input	TYPE1	
17	AO <sub>0</sub>	2	Output	TYPE2	
16	AO <sub>1</sub>	4	Output	TYPE2	
15	AO <sub>2</sub>	5	Output	TYPE2	
14	AO <sub>3</sub>	7	Output	TYPE2	
13	AO <sub>4</sub>	8	Output	TYPE2	A-out
12	AO <sub>5</sub>	10	Output	TYPE2	
11	AO <sub>6</sub>	11	Output	TYPE2	
10	AO <sub>7</sub>	13	Output	TYPE2	
9	AO <sub>8</sub>	14	Output	TYPE2	
8	BO <sub>0</sub>	15	Output	TYPE2	
7	BO <sub>1</sub>	16	Output	TYPE2	
6	BO <sub>2</sub>	18	Output	TYPE2	
5	BO3	19	Output	TYPE2	
4	BO <sub>4</sub>	21	Output	TYPE2	B-out
3	BO <sub>5</sub>	22	Output	TYPE2	
2	BO <sub>6</sub>	24	Output	TYPE2	
1	BO <sub>7</sub>	25	Output	TYPE2	
0	BO <sub>8</sub>	27	Output	TYPE2	

### Absolute Maximum Ratings(Note 1)

Storage Temperature	-65°C to +150°C
Ambient Temperature under Bias	$-55^{\circ}C$ to $+125^{\circ}C$
Junction Temperature under Bias	$-55^{\circ}C$ to $+150^{\circ}C$
$V_{CC}$ Pin Potential to Ground Pin	-0.5V to +7.0V
Input Voltage (Note 2)	-0.5V to +7.0V
Input Current (Note 2)	-30 mA to +5.0 mA
Voltage Applied to Any Output	
in Disabled or Power-Off State	-0.5V to +5.5V
in the HIGH State	–0.5V to $V_{CC}$
Current Applied to Output	
in LOW State (Max)	Twice the Rated I <sub>OL</sub> (mA)
DC Latchup Source Current	–500 mA
Over Voltage Latchup (I/O)	10V
ESD (HBM) Min	2000V

# Recommended Operating Conditions

Free Air Ambient Temperature	$-40^{\circ}C$ to $+85^{\circ}C$
Supply Voltage	+4.5V to +5.5V
Minimum Input Edge Rate	$(\Delta V / \Delta t)$
Data Input	50 mV/ns
Enable Input	20 mV/ns

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Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit of current limit is sufficient to protect inputs.

# **DC Electrical Characteristics**

Symbol	Paramete	er	Vcc	Min	Тур	Max	Units	Conditions
VIH	Input HIGH Voltage			2.0			V	Recognized HIGH Signal
VIL	Input LOW Voltage					0.8	V	Recognized LOW Signal
V <sub>CD</sub>	Input Clamp Diode Voltage Output		Min			-1.2	V	I <sub>IN</sub> = -18 mA
V <sub>OH</sub>	HIGH Voltage		Min	2.5			V	I <sub>OH</sub> = -3 mA
			Min	2.0			V	I <sub>OH</sub> = -32 mA
V <sub>OL</sub>	Output LOW Voltage		Min			0.8	V	I <sub>OL</sub> = 15 mA
I <sub>IH</sub>	Input HIGH Current	All Others	Max			5	μΑ	V <sub>IN</sub> = 2.7V (Note 3)
			Max			5	μΑ	$V_{IN} = V_{CC}$
		TMS, TDI	Max			5	μA	$V_{IN} = V_{CC}$
I <sub>BVI</sub>	Input HIGH Current Brea	kdown Test	Max			7	μΑ	V <sub>IN</sub> = 7.0V
I <sub>BVIT</sub>	Input HIGH Current Brea	kdown Test (I/O)	Max			100	μA	$V_{IN} = 5.5V$
IIL	Input LOW Current	All Others	Max			-5	μA	V <sub>IN</sub> = 0.5V (Note 3)
			Max			-5	μΑ	$V_{IN} = 0.0V$
		TMS, TDI	Max			-385	μΑ	$V_{IN} = 0.0V$
V <sub>ID</sub>	Input Leakage Test		0.0	4.75			V	I <sub>ID</sub> = 1.9 μA
								All Other Pins Grounded
I <sub>IH</sub> + I <sub>OZH</sub>	Output Leakage Current		Max			50	μΑ	$V_{OUT} = 2.7V$
I <sub>IL</sub> + L <sub>OZL</sub>	Output Leakage Current		Max			-50		$V_{OUT} = 0.5V$
I <sub>OZH</sub>	Output Leakage Current		Max			50	μA	$V_{OUT} = 2.7V$
I <sub>OZL</sub>	Output Leakage Current		Max			-50	μΑ	$V_{OUT} = 0.5V$
I <sub>OS</sub>	Output Short-Circuit Current		Max	-100		-275	mA	$V_{OUT} = 0.0V$
I <sub>CEX</sub>	Output HIGH Leakage Current		Max			50	μΑ	$V_{OUT} = V_{CC}$
I <sub>ZZ</sub>	Bus Drainage Test		0.0			100	μA	$V_{OUT} = 5.5V$
								All Others Grounded
I <sub>CCH</sub>	Power Supply Current		Max			250	μΑ	$V_{OUT} = V_{CC}$ ; TDI, TMS = $V_{CC}$
			Max			1.0	mA	$V_{OUT} = V_{CC}$ ; TDI, TMS = GND
I <sub>CCL</sub>	Power Supply Current		Max			65	mA	$V_{OUT}$ = LOW; TDI, TMS = $V_{CC}$
			Max			65.8	mA	V <sub>OUT</sub> = LOW; TDI, TMS = GND
I <sub>CCZ</sub>	Power Supply Current	ver Supply Current				250	μΑ	TDI, TMS = $V_{CC}$
			Max			1.0	mA	TDI, TMS = GND
сст	Additional I <sub>CC</sub> /Input	All Other Inputs	Max			2.9	mA	$V_{IN} = V_{CC} - 2.1V$
		TDI, TMS Inputs	Max			3	mA	$V_{IN} = V_{CC} - 2.1V$
CCD	Dynamic I <sub>CC</sub>	No Load	Max			0.2	mA/	Outputs Open
							MHz	One Bit Toggling, 50% Duty Cy

Normal Op		V <sub>cc</sub>	T <sub>A</sub>	=-40°C to +8	5°C		
Symbol	Parameter	(V)	C <sub>L</sub> = 50 pF			Units	
		(Note 4)	Min	Тур	Max		
PLH	Propagation Delay	5.0	1.2	3.7	6.5	ns	
PHL	D to Q		2.0	4.5	7.4	115	
PLH	Propagation Delay	5.0	1.3	4.1	7.4		
PHL	LE to Q		1.8	4.5	7.3	ns	
PLZ	Disable Time	5.0	1.6	4.9	9.0	ns	
PHZ			1.8	6.0	10.7	ns	
PZL	Enable Time	5.0	1.6	6.0	9.5		
PZH			1.0	5.0	9.3	ns	

# **AC Operating Requirements**

Symbol	Parameter	V <sub>CC</sub> (V) (Note 5)	$T_A = -40^{\circ}$ C to +85°C $C_L = 50 \text{ pF}$ Guaranteed Minimum	Units
s	Setup Time, H or L	5.0	1.7	ns
	Data to LE			
н	Hold Time, H or L	5.0	1.6	ns
	LE to Data			
w	LE Pulse Width	5.0	2.3	ns

Note 5: Voltage Range 5.0V ±0.5V

# **AC Electrical Characteristics**

Scan Test Operation:

		V <sub>CC</sub>	$T_A = -40^{\circ}C$ to $+85^{\circ}C$			
Symbol	Parameter	(V)	$C_L = 50 \text{ pF}$			Units
		(Note 6)	Min	Тур	Max	1
PLH	Propagation Delay	5.0	3.6	5.8	8.6	ns
t <sub>PHL</sub>	TCK to TDO		4.8	7.4	10.6	
t <sub>PLZ</sub>	Disable Time	5.0	2.7	5.6	9.0	ns
t <sub>PHZ</sub>	TCK to TDO		4.0	7.1	10.9	
t <sub>PZL</sub>	Enable Time	5.0	5.2	8.6	12.5	ns
t <sub>PZH</sub>	TCK to TDO		3.6	6.6	10.1	
t <sub>PLH</sub>	Propagation Delay		3.9	6.4	9.5	ns
t <sub>PHL</sub>	TCK to Data Out during Update-DR State	5.0	5.1	8.0	11.6	
t <sub>PLH</sub>	Propagation Delay		4.7	7.7	11.3	ns
t <sub>PHL</sub>	TCK to Data Out during Update-IR State	5.0	5.7	9.1	13.1	
t <sub>PLH</sub>	Propagation Delay	5.0	5.5	9.2	13.6	ns
t <sub>PHL</sub>	TCK to Data Out during Test Logic Reset State		6.7	10.7	15.6	
t <sub>PLZ</sub>	Disable Time		4.1	7.7	12.1	ns
t <sub>PHZ</sub>	TCK to Data Out during Update-DR State	5.0	4.7	8.4	12.7	
t <sub>PLZ</sub>	Disable Time		4.2	8.3	13.5	ns
t <sub>PHZ</sub>	TCK to Data Out during Update-IR State	5.0	4.7	9.0	14.0	
t <sub>PLZ</sub>	Disable Time	5.0	5.5	10.1	15.6	
t <sub>PHZ</sub>	TCK to Data Out during Test Logic Reset State		6.3	10.8	16.2	ns
t <sub>PZL</sub>	Enable Time		5.8	9.6	14.2	ns
t <sub>PZH</sub>	TCK to Data Out during Update-DR State	5.0	4.3	7.7	11.7	
t <sub>PZL</sub>	Enable Time		6.1	11.0	16.0	ns
t <sub>PZH</sub>	TCK to Data Out during Update-IR State	5.0	4.7	9.0	13.7	
t <sub>PZL</sub>	Enable Time	5.0	7.3	12.5	18.3	ns
t <sub>PZH</sub>	TCK to Data Out during Test Logic Reset State		5.8	10.5	15.8	

Scan Test Operation:		Vcc	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	1
Symbol	Parameter	(V) (Note 7)	C <sub>L</sub> = 50 pF	Units
Cymbol			Guaranteed Minimum	
t <sub>S</sub>	Setup Time, Data to TCK (Note 8)	5.0	2.7	ns
t <sub>H</sub>	Hold Time, Data to TCK (Note 8)	5.0	2.4	ns
t <sub>S</sub>	Setup Time, H or L AOE 1, BOE 1 to TCK (Note 9)	5.0	5.1	ns
t <sub>H</sub>	Hold Time, H or L TCK to AOE 1, BOE 1 (Note 9)	5.0	1.8	ns
t <sub>S</sub>	Setup Time, H or L Internal AOE, BOE, to TCK (Note 10)	5.0	3.5	ns
t <sub>H</sub>	Hold Time, H or L TCK to Internal AOE, BOE (Note 10)	5.0	1.8	ns
t <sub>S</sub>	Setup Time ALE, BLE (Note 11) to TCK	5.0	5.1	ns
t <sub>H</sub>	Hold Time TCK to ALE, BLE (Note 11)	5.0	1.8	ns
t <sub>S</sub>	Setup Time, H or L TMS to TCK	5.0	7.9	ns
t <sub>H</sub>	Hold Time, H or L TCK to TMS	5.0	1.8	ns
t <sub>S</sub>	Setup Time, H or L TDI to TCK	5.0	6.0	ns
t <sub>H</sub>	Hold Time, H or L TCK to TDI	5.0	3.0	ns
t <sub>W</sub>	Pulse Width TCK H	5.0	10.3 10.3	ns
f <sub>MAX</sub>	Maximum TCK Clock Frequency	5.0	50	MHz
t <sub>PU</sub>	Wait Time, Power Up to TCK	5.0	100	ns
t <sub>DN</sub>	Power Down Delay	0.0	100	ms

Note 8: This delay represents the timing relation Note 9: Timing pertains to BSR 38 and 41 only.

Note 10: This delay represents the timing relationship between AOE/BOE and TCK for scan cells 36 and 39 only.

Note 11: Timing pertains to BSR 37 and 40 only.

Note: All Input Timing Delays involving TCK are measured from the rising edge of TCK.

# Capacitance

Symbol	Parameter	Тур	Units	Conditions, T <sub>A</sub> = 25°C
CIN	Input Capacitance	5.8	pF	$V_{CC} = 0.0V$
COUT	Output Capacitance (Note 12)	13.8	pF	$V_{CC} = 5.0V$

Note 12: C<sub>OUT</sub> is measured at frequency f = 1 MHz, per MIL-STD-883B, Method 3012

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